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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Inventor: Tatau NISHINAGA Group Art Unit: 1765
Appln. No.: 09/511,912 Examiner: M. Anderson
Filed: February 23, 2000
For: A METHOD FOR FORMING A SINGLE CRYSTALLINE FILM

#21/29
Mda
12/27/02

SUPPLEMENTAL AMENDMENT UNDER 37 CFR § 1.111

Assistant Commissioner of Patents
Washington, D.C. 20231

Sir:

Supplemental to the Amendment filed December 12, 2002, the Applicant requests further amendment of the above-captioned application as follows:

IN THE CLAIMS:

Kindly add the following new claims.

--20. The method of claim 1, wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, SrTiO₃, and sapphire; and

the single crystalline film is formed from one of the group of Si, GaAs, Ga_{1-x}Al_xAs, ZnSe, ZnS, CdTe, ZnS_{1-x}Se_x, and YBCO.

21. The method of claim 1, wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, and SrTiO₃; and